

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

1. (Currently Amended) A radiation-emitting semiconductor device ~~component~~ comprising:  
  
a multilayer structure, comprising:  
  
an active, radiation-generating layer;  
  
a reflective layer or interface;  
  
a first main area coupled to the reflective layer or interface; and  
  
a second main area remote from the first main area for coupling out the radiation generated in the active, radiation-generating layer,  
  
wherein the multilayer structure is an epitaxial layer structure, the semiconductor device ~~component~~ is free of a deposition substrate of the multilayer structure, and a region of the multilayer structure that adjoins the second main area of the multilayer structure is patterned one- or two-dimensionally.
  
2. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 1, wherein the region of the multilayer structure that adjoins the second main area of the multilayer structure has convex elevations.

3. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 2, wherein the elevations have the form of truncated pyramids or truncated cones or a trapezoidal cross-sectional form.

4. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 2, wherein the elevations have the form of cones or a triangular cross-sectional form.

5. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 2, wherein the elevations have the form of sphere segments or a circle segment cross-sectional form.

6. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 2, wherein the elevations have an aperture angle ( $\alpha$ ) of between approximately 30° and approximately 70°.

7. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 6, wherein the elevations have an aperture angle ( $\alpha$ ) of between approximately 40° and approximately 50°.

8. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 2, wherein the height (h1) of the elevations is at least as large as the height (h2) of a plane region of the multilayer structure between the active, radiation-generating layer and the elevations.

9. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 8, wherein the height (h1) of the elevations is approximately twice as large as the height (h2) of the plane region of the multilayer structure between the active, radiation-generating layer and the elevations.

10. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 2, wherein a grid dimension (d) of the elevations is at most approximately five times as large as the height (h1) of the elevations.

11. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 10, wherein the grid dimension (d) of the elevations is at most approximately three times as large as the height (h1) of the elevations.

12. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 1, wherein the reflective layer or interface coupled to the first main area of the multilayer structure has a reflectivity of at least 70%.

13. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 1, wherein the reflective layer or interface coupled to the first main area of the multilayer structure has a reflectivity of at least 85%.

14. (Currently Amended) The semiconductor device component as claimed claim 1, wherein the multilayer structure is applied by its first main area via the reflective layer on a carrier substrate or a carrier substrate forms the reflective interface with the first main area.

15. (Currently Amended) The semiconductor device component as claimed in claim 14, wherein the reflective layer or the carrier substrate also serves as a contact area of the semiconductor device component.

16. (Currently Amended) The semiconductor device component as claimed claim 1, wherein a conductive, transparent layer is applied on the second main area of the multilayer structure.

17. (Currently Amended) The semiconductor device component as claimed in claim 1, wherein a transparent protective layer is applied on the second main area of the multilayer structure.

18. (Currently Amended) A radiation-emitting semiconductor device component comprising:

a multilayer structure, comprising:

an active, radiation-generating layer;

a reflective layer or interface;

a first main area coupled to the reflective layer or interface;

a second main area remote from the first main area for coupling out the radiation generated in the active, radiation-generating layer; and

a transparent layer disposed between the first main area and the reflective layer or interface, said transparent layer being patterned one- or two-dimensionally,

wherein the multilayer structure is an epitaxial layer structure, and the semiconductor device component is free of a deposition substrate of the multilayer structure.

19. (Currently Amended) The semiconductor device component as claimed in claim 18, wherein the transparent layer is conductive.

20. (Currently Amended) The semiconductor device component as claimed in claim 18, wherein the transparent layer between the first main area of the multilayer structure and the reflective layer or interface comprises convex elevations.

21. (Currently Amended) The semiconductor device component as claimed in claim 20, wherein the elevations have the form of truncated pyramids or truncated cones or a trapezoidal cross-sectional form.

22. (Currently Amended) The semiconductor device component as claimed in claim 20, wherein the elevations have an aperture angle ( $\alpha$ ) of between approximately 30° and approximately 70°.

23. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 20, wherein the elevations have an aperture angle ( $\alpha$ ) of between approximately 40° and approximately 50°.

24. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 20, wherein the height (h1) of the elevations is at least as large as the height (h2) of a plane region of the multilayer structure between the active, radiation-generating layer and the elevations.

25. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 24, wherein the height (h1) of the elevations is approximately twice as large as the height (h2) of the plane region of the multilayer structure between the active, radiation-generating layer and the elevations.

26. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 20, a grid dimension (d) of the elevations is at most approximately five times as large as the height (h1) of the elevations.

27. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 26, wherein the grid dimension (d) of the elevations is at most approximately three times as large as the height (h1) of the elevations.

28. (Currently Amended) The semiconductor device component as claimed in claim 18, wherein the layer or interface coupled to the first main area of the multilayer structure has a reflectivity of at least 70%.

29. (Currently Amended) The semiconductor device component as claimed in claim 28, wherein the layer or interface coupled to the first main area of the multilayer structure has a reflectivity of at least 85%.

30. (Currently Amended) The semiconductor device component as claimed in claim 18, wherein the reflective layer is applied on a carrier substrate or the reflective interface is formed by a carrier substrate.

31. (Currently Amended) The semiconductor device component as claimed in claim 30, wherein the reflective layer or the carrier substrate also serves as a contact area of the semiconductor device component.

32. (Currently Amended) The semiconductor device component as claimed in claim 18, wherein a transparent protective layer is applied on the second main area of the multilayer structure.

33. (Currently Amended) The semiconductor device component as claimed in claim 1, wherein the multilayer structure is based on GaN.

34. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 18, wherein the multilayer structure is based on GaN.

35. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 18, wherein the reflective layer or interface is substantially planar.

36. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 20, wherein, due to the convex elevations, the transparent layer comprises first and second regions, the first regions having a thickness greater than a thickness of the second regions.

37. (Currently Amended) The semiconductor device ~~component~~ as claimed in claim 18, wherein the active, radiation-generating layer is a continuous layer, and the transparent layer comprises a plurality of elevations that overlap with the active, radiation-generating layer.